



APPLICANT'S ART CITATION

(Use several sheets if necessary)

Application 09/292,186

OFGS File No. IR-1609 (2-1941)

Applicant
Daniel M. KinzerFiling Date
April 15, 1999

Group Art Unit

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number							Date	Name	Class	Sub-class	Filing Date If Appropriate
SA	4	9	6	1	1	0	0	10/2/90	Baliga et al.	H01L		
SA	4	5	6	8	9	5	8	2/4/96	Baliga et al.	H01L		
SA	4	8	5	9	6	2	1	8/22/89	Einthoven	H01L		

FOREIGN PATENT DOCUMENTS

	Document Number							Date	Country	Class	Sub-class	Translation	
												Yes	No
SA	2	0	7	7	4	9	5	12/16/81	Great Britain			X	
SA	9	6	3	8	8	6	2	12/5/96	PCT			X	
SA	9	6	3	0	9	4	7	10/3/96	PCT			X	
SA	9	4	1	3	0	1	7	6/9/94	PCT			X	

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Examiner

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SAL		A HIGH-DENSITY ULTRA-LOW Rdson 30 VOLT N-CHANNEL TRENCH FETs FOR DC/DC CONVERTER APPLICATIONS, EL SEGUNDO CA, PAGES 1-4, SODHI R; MALIK R; ASSELANIS D; and KINZER D, "PROCEEDINGS OF INTERNATIONAL SYMPOSIUM OF POWER SEMICONDUCTOR DEVICES AND ICs (ISPSD)", MAY 26, 1999. IEEE CATALOG #99CH36312, PP 303-306									
SAL		ULTRA-LOW Rdson 12 v P-CHANNEL TRENCH MOSFET, EL SEGUNDO CA, PAGES 1-4, KINZER D; ASSELANIS D; and CARTA R, "PROCEEDINGS OF INTERNATIONAL SYMPOSIUM OF POWER SEMICONDUCTOR DEVICES AND ICs (ISPSD)", MAY 26, 1999. IEEE CATALOG #99CH36312, PP 307-310									
SAL		INTEGRATED DESIGN ENVIRONMENT FOR DC/DC CONVERTER FET OPTIMIZATION, EL SEGUNDO CA, PAGES 1-4, SODHI R; BROWH S Sr.; and KINZER D.; DALLAS TX, MARTINEZ R; STANFORD CA, WIEMER M, "PROCEEDINGS OF INTERNATIONAL SYMPOSIUM OF POWER SEMICONDUCTOR DEVICES AND ICs (ISPSD)", MAY 26, 1999. IEEE CATALOG #99CH36312, PP 241-244									
Examiner <i>Shoushang</i>		Date Considered 6/2/00									
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